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Total No. of Questions—12]

[Total No. of Printed Pages—8

[3962]-152**S.E. (E&TC/Elex.) (First Semester) EXAMINATION, 2011****SOLID STATE DEVICES AND CIRCUITS****(2008 PATTERN)****Time : Three Hours****Maximum Marks : 100**

N.B. :— (i) Answers to the two Sections should be written in separate answer-books.

(ii) Neat diagrams must be drawn wherever necessary.

(iii) Figures to the right indicate full marks.

(iv) Use of logarithmic tables, slide rule, Mollier charts, electronic pocket calculator and steam tables is allowed.

(v) Assume suitable data, if necessary.

SECTION I

1. (a) Explain construction, operation and characteristics of photo-diode. [6]

(b) Explain the following Non-ideal characteristics of MOSFET :

(i) Finite output resistance

(ii) Body effect

(iii) Subthreshold conduction

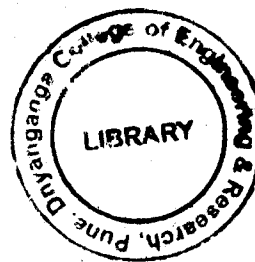
(iv) Breakdown effect. [8]

(c) An ideal Ge-diode at a temperature of 120°C has a reverse saturation current of $30\text{ }\mu\text{A}$ at a temperature of 120°C . Find the dynamic resistance for a 0.2 V bias in :

(i) The forward bias direction

(ii) Reverse bias direction. [4]

P.T.O.



Or

2. (a) Why are MOSFETs used as VLSI device ? [4]
 (b) While handling CMOS devices, what precautions should be taken ? [6]
 (c) Analyze the circuit shown in Fig. 1. Assume circuit and diode parameters of $V_{ps} = 5\text{ V}$, $R = 5\text{ k}\Omega$, $V_r = 0.6\text{ V}$ and $V_i = 0.5 \sin \omega t$ volts. [8]

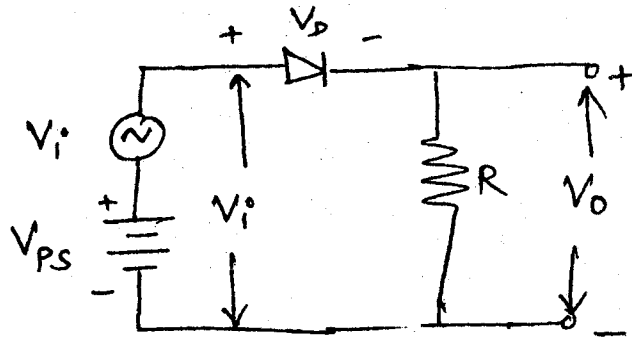


Fig. 1

3. (a) Explain with neat diagram BiCMOS inverter. [8]
 (b) For the circuit shown in Fig. 2, calculate I_D , V_{DS} , V_{Cr} , V_S . For the MOSFET, $I_{DSS} = 20\text{ mA}$, $V_{GS(OFF)} = -6\text{ V}$. [8]

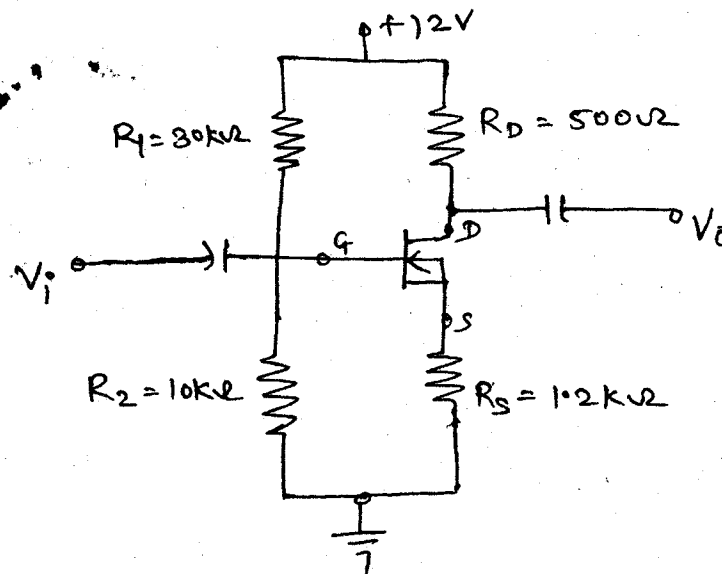


Fig. 2

Or

4. (a) Explain MOSFET scaling and small geometry effects. [8]
- (b) For the circuit shown in Fig. 3, calculate V_G , I_D , V_{GS} , V_{DS} . For MOSFET $V_{GS(Th)} = 5\text{ V}$, $I_{D(ON)} = 3\text{ mA}$, $V_{GS(ON)} = 10\text{ V}$. [8]

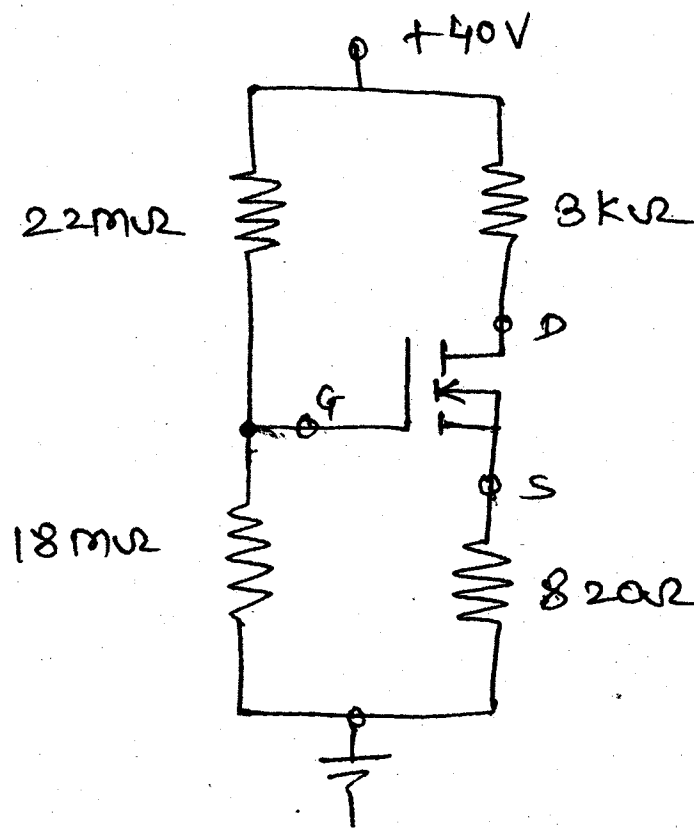


Fig. 3

5. (a) Why is bias stabilization in BJT amplifier needed? Define three bias stabilization factors and explain its significance. [8]

- (b) Derive an expression for current gain, voltage gain, input impedance and output impedance of CE amplifier for small signal h -model. [8]

Or

6. (a) For the amplifier circuit shown in Fig. 4, calculate :

$$A_{vs} = \frac{V_o}{V_s}, A_{IS} = \frac{I_o}{I_s}, R_i', R_o'$$

For the BJT $h_{ie} = 1.1 \text{ k}\Omega$, $h_{fe} = 50$,

$h_{re} = 2.4 \times 10^{-4}$, $h_{oe} = 25 \text{ }\mu\text{A/V}$. [8]

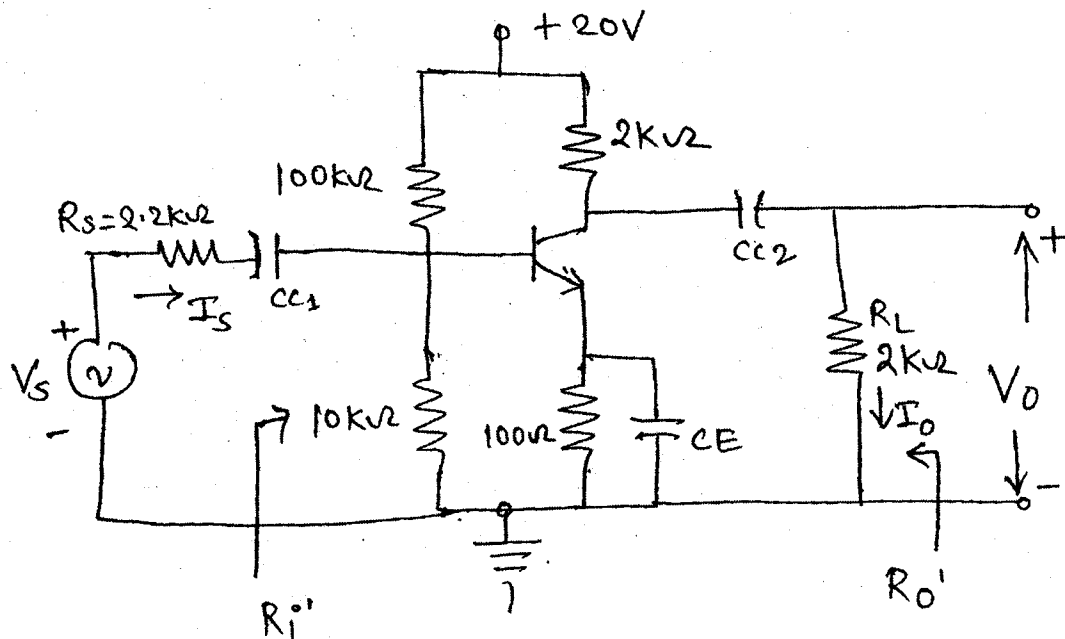


Fig. 4

- (b) Explain the need of multistaging of amplifiers. What is the selection criterion for transistor configuration in multistage amplifiers. [8]

SECTION II

7. (a) What are the advantages of square wave testing over frequency response method ? Explain in brief. [4]
- (b) Explain the concept of 'Dominant Pole' in BJT amplifier with sketch. [4]
- (c) A high frequency amplifier uses a transistor which is driven from a source with $R_S = 1 \Omega$, calculate value of f_H , A_{VS}^{low} and A_{VS}^{high} if $R_L = 0$ and $R_L = 1 \text{ k}\Omega$.
Assume hybrid $-\pi$ parameters : $r_{b'e} = 1 \text{ k}\Omega$, $r_{b'b} = 100 \Omega$, $C_e = 100 \text{ pF}$, $C_c = 3 \text{ pF}$, $\beta = 50 \text{ mA/V}$. [8]

Or

8. (a) Derive the expression for CE short circuit current gain A_i as a function of frequency. [8]
- (b) An RC-coupled amplifier has $A_{Vmid} = 80$, $R_{in} = 10 \text{ k}\Omega$, it is fed from ideal voltage source through $C_C = 0.1 \mu\text{F}$. Calculate lower 3 dB frequency gain at 300 Hz and frequency at which gain is down by 10 dB from its mid frequency value. [8]
9. (a) Explain the typical methodology used for feedback amplifier analysis. [6]

- (b) A Colpitts oscillator shown in Fig. 5. What is the approximate frequency ? What will be the frequency, if the value of L is doubled ? What should be the value of inductance to double the frequency value ? [8]

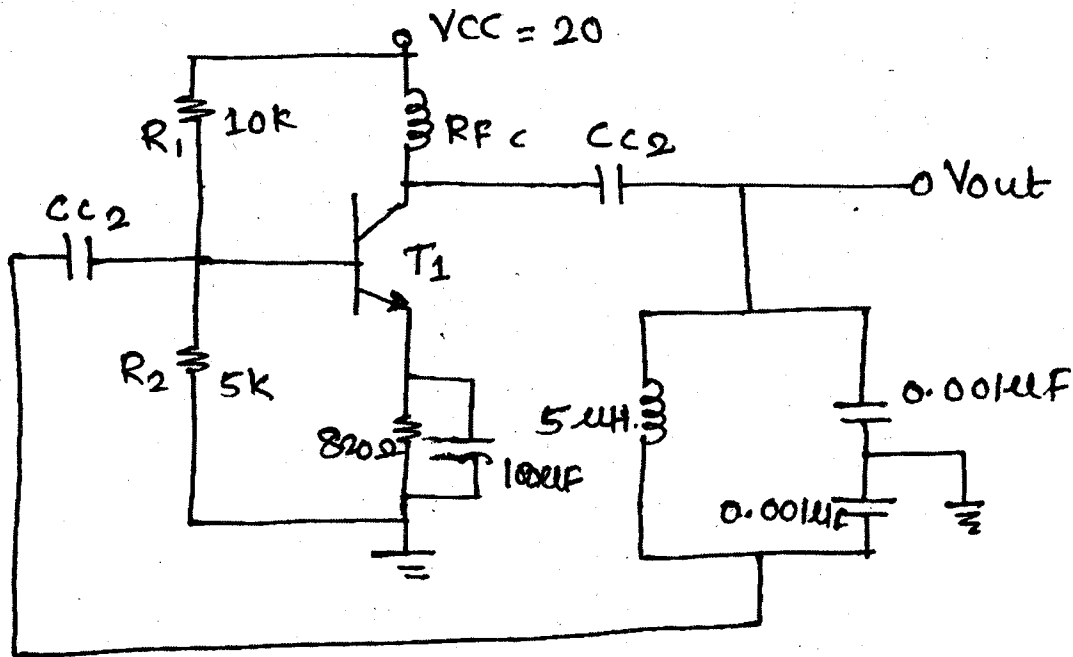


Fig. 5

- (c) Write a short note on crystal oscillator. [4]

Or

10. (a) Define the stability of system. Explain it in terms of Boded plot. [6]

- (b) For the feedback amplifier shown in Fig. 6,

$$R_s = 0, h_{fe} = 50, h_{ie} = 1.1 \text{ k}\Omega, h_{re} = h_{oe} = 0.$$

and transistors are identical. Calculate A_{vf} , R_{of}' , R_{if}' . [10]

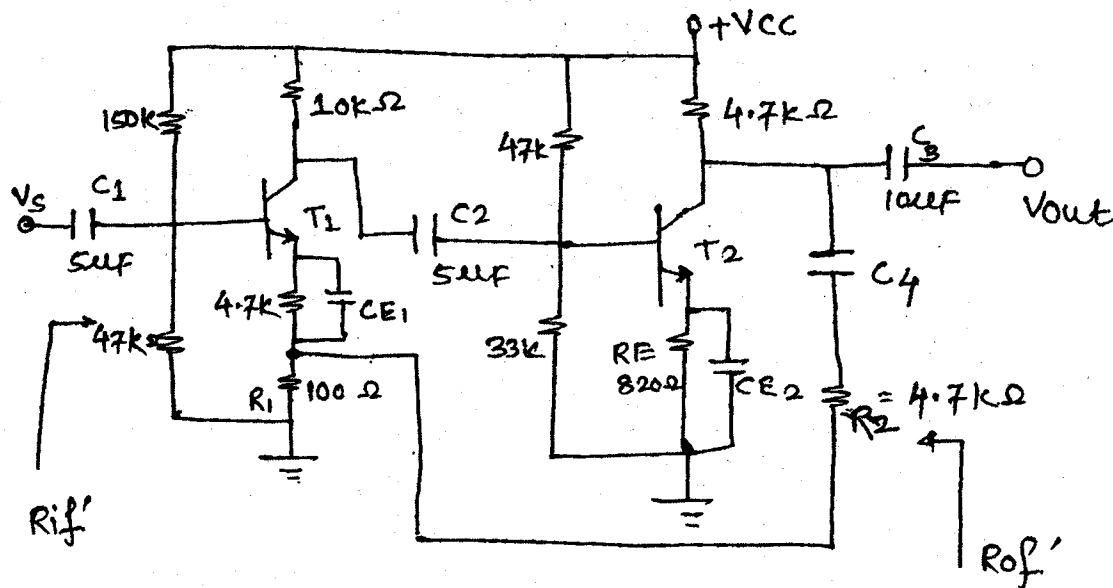


Fig. 6

- (c) What are the advantages of negative feedback ? [2]
11. (a) Discuss the safe operating area of transistor. [4]
- (b) A complementary symmetry class AB. Audio frequency power amplifier uses two matched BJTs and dual power supply of ± 30 V, and feeds a common load of 8Ω . If the i/p voltage to the amplifier is 8 V (rms), calculate :
- DC power input
 - AC power output
 - Max. Possible AC power O/P
 - Efficiency
 - Power dissipation by both transistors. [8]
- (c) Write a short note on thermal resistance. [4]

Or

12. (a) With the help of neat circuit diagram explain the operation of complementary symmetry (class AB) power amplifier. Explain the significance of class AB. [8]

(b) A sinusoidal signal $V_s = 1.95 \sin 400t$ is applied to a power amplifier. The resulting current is $I_o = 12 \sin 400t + 1.2 \sin 800t + 0.9 \sin 1200t + 0.4 \sin 1600t$.

Calculate :

(i) Total Harmonic Distortion

(ii) Percentage increase in power because of distortion. [8]

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